

ZVP2106A Information



For Reference Only

Part Number ZVP2106A

Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 60V 280MA TO92-3 **Package** TO-226-3, TO-92-3 (TO-226AA)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









ZVP2106A Specifications

Manufacturer Part Number ZVP2106A Manufacturer Diodes Incorporated Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 280mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 100pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 700mW (Ta) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) To source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 280mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 100pF @ 18V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ 1d, Vgs To Onm (Ta) Rds On (Max) @ 1d, Vgs To Onm (Ta) Rds On (Max) @ 1d, Vgs Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Manufacturer Part Number	ZVP2106A
Package Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 280mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ ImA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 100pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 700mW (Ta) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-A, TO-92-3 (TO-226AA)	Manufacturer	Diodes Incorporated
Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 280mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 100pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 700mW (Ta) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Category	Discrete Semiconductor Products
Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 280mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 100pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 700mW (Ta) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 (TO-226AA)		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C280mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds100pF @ 18VVgs (Max)±20VFET Feature-Power Dissipation (Max)700mW (Ta)Rds On (Max) @ Id, Vgs5 Ohm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Package	TO-226-3, TO-92-3 (TO-226AA)
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 280mA (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package Package / Case MOSFET (Metal Oxide) 60V 280mA (Ta) 10V 280mA (Ta) 10V 280mA (Ta) 100pF @ 18V 220V 5 Ohm @ 500mA, 10V 700mW (Ta) Through Hole TO-92-3 Package / Case	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C280mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds100pF @ 18VVgs (Max)±20VFET Feature-Power Dissipation (Max)700mW (Ta)Rds On (Max) @ Id, Vgs5 Ohm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature Current - Continuous Drain (Id) @ 25°C 280mA (Ta) 10V 3.5V @ 1mA 100pF @ 18V +20V FET Feature	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature Supplier Device Package Package / Case TO-92-3 TO-92-3 (TO-226AA)	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 3.5V @ 1mA 5.0PF @ 18V \$ \$ 20V FET Feature - Company (Ta) Found (Ta) Found (Ta) Though Hole Supplier Device Package TO-92-3 TO-92-3 (TO-226AA)	Current - Continuous Drain (Id) @ 25°C	280mA (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Vgs(th) (Max) @ Id	3.5V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)700mW (Ta)Rds On (Max) @ Id, Vgs5 Ohm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) 700mW (Ta) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Input Capacitance (Ciss) (Max) @ Vds	100pF @ 18V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs5 Ohm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Power Dissipation (Max)	700mW (Ta)
Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Rds On (Max) @ Id, Vgs	5 Ohm @ 500mA, 10V
Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-226-3, TO-92-3 (TO-226AA)	Mounting Type	Through Hole
	Supplier Device Package	TO-92-3
Report errors?	Package / Case	TO-226-3, TO-92-3 (TO-226AA)
		Report errors?

ZVP2106A Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

ZVP2106A Payment Methods



















ZVP2106A Shipping Methods













If you have any question about ZVP2106A, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com